

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a semiconductor substrate, source/drain regions provided in the semiconductor substrate, a gate insulating film provided on a channel region between the source/drain regions, a gate electrode provided on the gate insulating film, a conductive layer of a metal silicide provided on the gate electrode and the source/drain regions, an insulating film containing carbon provided on the semiconductor substrate so as to be in contact with at least the conductive layer, and an interlayer insulating film provided on the semiconductor substrate so as to cover the insulating film containing carbon.